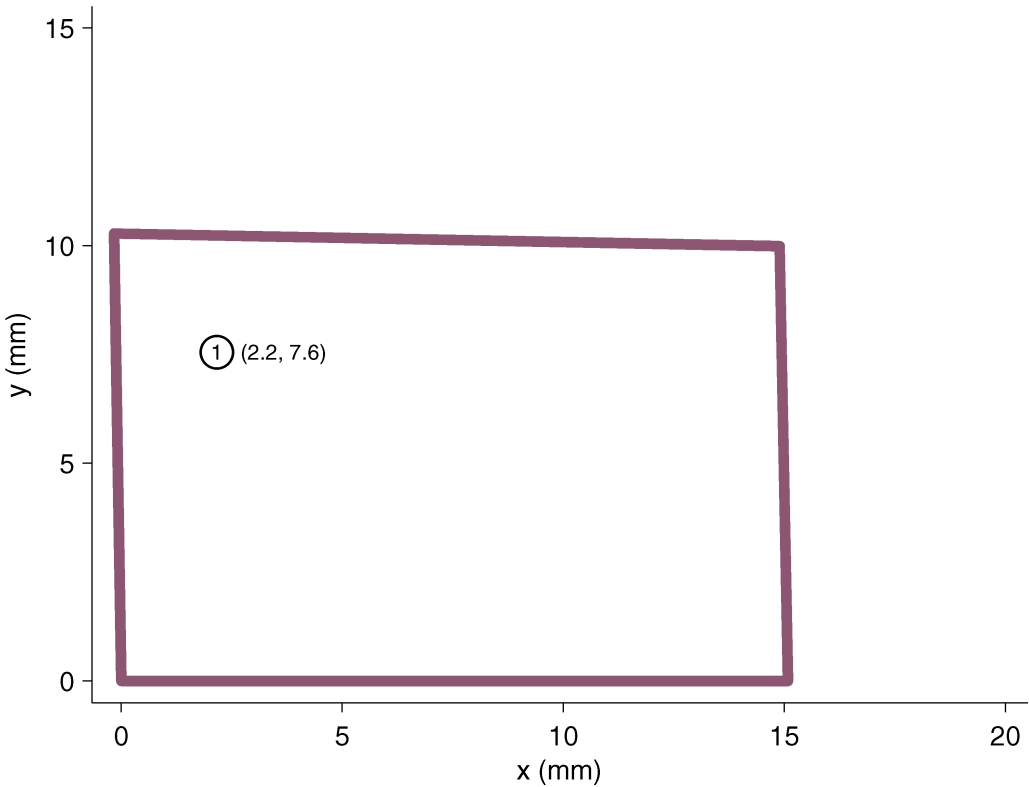


Sample S4363 Datasheet

Parent Wafer

Manufacturer	IDB Technologies Ltd.
Diameter	76mm
Si Orientation	<100>
Si Thickness	380 μm
Si Doping	N-type, phosphorus
Resistivity	0.001-0.050 Ωcm
Oxide	280-310 nm dry thermal oxide

Substrate Map



Flake 1 of 1: x=2.2mm, y=7.6mm, monolayer flake with bilayer region

